

# Thilo Hepp

## List of Publications by Year in descending order

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9  
papers

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1937685  
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docs citations

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times ranked

35  
citing authors

#	ARTICLE	IF	CITATIONS
1	Bismuth surface segregation and disorder analysis of quaternary (Ga,In)(As,Bi)/InP alloys. Journal of Applied Physics, 2019, 126, 135705.	2.5	7
2	Comparison of carrier-recombination in Ga(As,Bi)/Ga(N,As)-type-II quantum wells and W-type heterostructures. Applied Physics Letters, 2021, 118, .	3.3	6
3	Decomposition Mechanisms of Di- <i>tert</i> -butylaminoarsane (DTBAA). Organometallics, 2019, 38, 3181-3186.	2.3	4
4	Metalorganic vapor phase epitaxy growth and characterization of quaternary (Ga,In)(As,Bi) on GaAs substrates. Journal of Applied Physics, 2019, 126, 085707.	2.5	4
5	Ga(N,P) Growth on Si and Decomposition Studies of the Nâ€P Precursor Di- <i>tert</i> -butylaminophosphane (DTBAP). Organometallics, 2020, 39, 1772-1781.	2.3	3
6	Room-temperature laser operation of a (Ga,In)As/Ga(As,Bi)/(Ga,In)As W-type laser diode. Electronics Letters, 2022, 58, 70-72.	1.0	3
7	Dilute Bismuth Containing W-Type Heterostructures for Long-Wavelength Emission on GaAs Substrates. Crystal Growth and Design, 0, , .	3.0	1
8	Revealing the Significance of Catalytic and Alkyl Exchange Reactions during GaAs and GaP Growth by Metal Organic Vapor Phase Epitaxy. ACS Omega, 2021, 6, 28229-28241.	3.5	1
9	Type-II GaAs <sub>1-x</sub> Bi <sub>x</sub> /GaN <sub>y</sub> As <sub>1-y</sub> "W" quantum wells for strain-compensated GaAs-based telecom lasers. , 2021, , .		0